

SOT-89-3L Plastic-Encapsulate Transistors

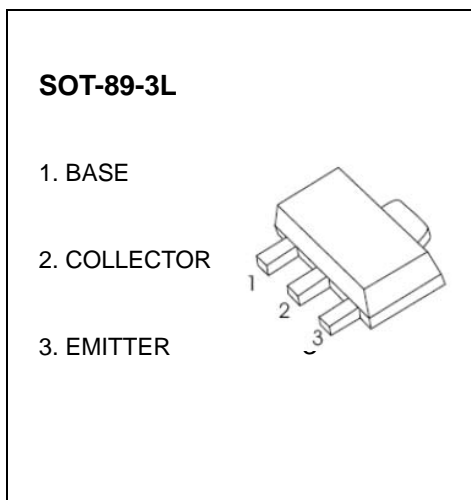
2SB1188 TRANSISTOR (PNP)

FEATURES

- Low $V_{CE(sat)}$.
- Complements the 2SD1766

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-32	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector Power Dissipation	500	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}$, $I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $I_B=0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}$, $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20\text{V}$, $I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}$, $I_C=0$			-1	μA
DC current gain *	h_{FE}	$V_{CE}=-3\text{V}$, $I_C=-0.5\text{A}$	82		390	
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C=-2\text{A}$, $I_B=-0.2\text{A}$			-0.8	V
Transition frequency	f_T	$V_{CE}=-5\text{V}$, $I_C=-0.5\text{A}$, $f=30\text{MHz}$		100		MHz
Output capacitance	C_{ob}	$V_{CB}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$		50		pF

* Measured using pulse current.

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	BCP	BCQ	BCR

Typical Characteristics

2SB1188

